

# ***Alpha & Omega Semiconductor Product Reliability Qualification Report***

**AOZ32101MDV** rev A

**Plastic Encapsulated Device**

**ALPHA & OMEGA Semiconductor, Inc**

**[www.aosmd.com](http://www.aosmd.com)**

This AOS product reliability report summarizes the qualification results for AOZ32101MDV in DFN3x3-10L package. Accelerated environmental tests are performed on a specific sample size and samples are electrically tested before and after each time point. Review of final electrical test results confirm that AOZ32101MDV pass the AOS quality and reliability requirements. The released products will be categorized by its process family and routinely monitored for continuous improvement of product quality.

## I. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTOL	T <sub>J</sub> = 125°C, V <sub>IN</sub> = V <sub>ccmax</sub>	168 / 500 / 1000 hours	231 pcs	0	JESD22-A108
Preconditioning	T <sub>A</sub> = 85°C, RH = 85% + 3 cycle reflow @ 260°C (MSL 1)	168 hours	231*4 pcs	0	JESD22-A113 J-STD-020
HAST	T <sub>A</sub> = 130°C, RH = 85%, P = 33.3psia, V <sub>IN</sub> = V <sub>ccmax</sub>	96 hours	231 pcs	0	JESD22-A110
Autoclave	T <sub>A</sub> = 121°C, RH = 100%, P = 29.7psia	96 hours	231 pcs	0	JESD22-A102
Temperature Cycle	T <sub>A</sub> = -65°C to 150°C, air to air	250 / 500 / 1000 cycles	231 pcs	0	JESD22-A104
HTSL	Temp = 150°C	500 / 1000 / hours	231 pcs	0	JESD22-A103

## II. Reliability Evaluation

**FIT rate (per billion): 50.97**

**MTTF = 2240 years**

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

**Failure Rate** =  $\text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)] = 50.97$

**MTTF** =  $10^9 / \text{FIT} = 2240$  years

**Chi<sup>2</sup>** = Chi Squared Distribution, determined by the number of failures and confidence interval

**N** = Total Number of units from burn-in tests

**H** = Duration of burn-in testing

**Af** = Acceleration Factor from Test to Use Conditions (E<sub>a</sub> = 0.7eV and T<sub>use</sub> = 55°C)

Acceleration Factor [**Af**] =  $\text{Exp} [E_a / k (1/T_{J u} - 1/T_{J s})]$

**Acceleration Factor ratio list:**

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	125 deg C
<b>Af</b>	<b>77</b>	<b>26</b>	<b>9.8</b>	<b>3.9</b>	<b>1.7</b>	<b>1</b>

T<sub>J s</sub> = Stressed junction temperature in degree (Kelvin), K = C + 273.16

T<sub>J u</sub> = The use junction temperature in degree (Kelvin), K = C + 273.16

**k** = Boltzmann's constant, 8.617164 X 10<sup>-5</sup>eV / K

### III. ESD and Latch Up Test Results

Test	Test Conditions	Total Sample Size	Number of Failures	Reference Standard
Electrostatic Discharge Human Body Model	T <sub>A</sub> = 25°C, +/-1kV	3	0	JS-001-2017
Electrostatic Discharge Charged Device Model	T <sub>A</sub> = 25°C, +/-1kV	3	0	JS-002-2018
Latch Up	T <sub>A</sub> = 25°C, +/-100mA, 1.5xOV	6	0	JESD78
Latch Up	T <sub>A</sub> = 125°C, +/-100mA, 1.5xOV	6	0	JESD78

(1) ATE results are used to determine PASS/FAIL. Parametric shift <10%.

